MV2101 (SILICON) thru MV2115

VVC

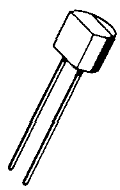
SILICON EPICAP DIODES

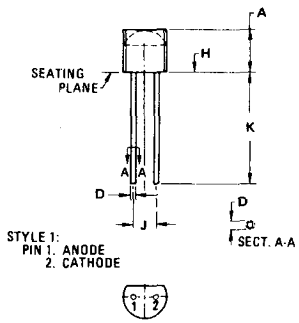
. . . designed in the popular PLASTIC PACKAGE for high volume requirements of FM Radio and TV tuning and AFC, general frequency control and tuning applications; providing solid-state reliability in replacement of mechanical tuning methods.

- High Q with Guaranteed Minimum Values
- Controlled and Uniform Tuning Ratio
- Standard Capacitance Tolerance – 10%
- Complete Typical Design Curves

VOLTAGE-VARIABLE CAPACITANCE DIODES

6.8–100 pF
30 VOLTS





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.45	4.70	0.175	0.185
D	0.41	0.48	0.016	0.019
J	2.29	2.79	0.090	0.110
K	12.70	–	0.500	–

CASE 182-03

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Volts
Forward Current	I_F	200	mA
Device Dissipation @ $T_A = 25^oC$ Derate above 25^oC	P_D	280 2.8	mW $mW/^oC$
Junction Temperature	T_J	+125	^oC
Storage Temperature Range	T_{stg}	-65 to +150	^oC

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic—All Types	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	BV_R	30	–	–	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc, T_A = 25°C)	I_R	–	–	0.10	μAdc
Series Inductance (f = 250 MHz, Lead Length ≈ 1/16")	L_S	–	6.0	–	nH
Case Capacitance (f = 1.0 MHz, Lead Length ≈ 1/16")	C_C	–	0.18	–	pF
Diode Capacitance Temperature Coefficient (V_R = 4.0 Vdc, f = 1.0 MHz)	TC_C	–	280	400	ppm/°C

	C_T, Diode Capacitance V_R = 4.0 Vdc, f = 1.0 MHz pF			Q, Figure of Merit V_R = 4.0 Vdc, f = 50 MHz	TR, Tuning Ratio C_2/C_{30} f = 1.0 MHz		
Device	Min	Nom	Max	Min	Min	Typ	Max
MV2101	6.1	6.8	7.5	450	2.5	2.7	3.2
MV2102	7.4	8.2	9.0	450	2.5	2.8	3.2
MV2103	9.0	10.0	11.0	400	2.5	2.9	3.2
MV2104	10.8	12.0	13.2	400	2.5	2.9	3.2
MV2105	13.5	15.0	16.5	400	2.5	2.9	3.2
MV2106	16.2	18.0	19.8	350	2.5	2.9	3.2
MV2107	19.8	22.0	24.2	350	2.5	2.9	3.2
MV2108	24.3	27.0	29.7	300	2.5	3.0	3.2
MV2109	29.7	33.0	36.3	200	2.5	3.0	3.2
MV2110	35.1	39.0	42.9	150	2.5	3.0	3.2
MV2111	42.3	47.0	51.7	150	2.5	3.0	3.2
MV2112	50.4	56.0	61.6	150	2.6	3.0	3.3
MV2113	61.2	68.0	74.8	150	2.6	3.0	3.3
MV2114	73.8	82.0	90.2	100	2.6	3.0	3.3
MV2115	90.0	100.0	110.0	100	2.6	3.0	3.3

PARAMETER TEST METHODS

1. L_S, SERIES INDUCTANCE

L_S is measured on a shorted package at 250 MHz using an impedance bridge (Boonton Radio Model 250A RX Meter).

2. C_C, CASE CAPACITANCE

C_C is measured on an open package at 1.0 MHz using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

3. C_T, DIODE CAPACITANCE

($C_T = C_C + C_J$). C_T is measured at 1.0 MHz using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

4. TR, TUNING RATIO

TR is the ratio of C_T measured at 2.0 Vdc divided by C_T measured at 30 Vdc.

5. Q, FIGURE OF MERIT

Q is calculated by taking the G and C readings of an admittance bridge at the specified frequency and substituting in the following equations:

$$Q = \frac{2\pi fC}{G}$$

(Boonton Electronics Model 33AS8). Use Lead Length ≈ 1/16".

6. TC_C, DIODE CAPACITANCE TEMPERATURE COEFFICIENT

TC_C is guaranteed by comparing C_T at V_R = 4.0 Vdc, f = 1.0 MHz, T_A = -65°C with C_T at V_R = 4.0 Vdc, f = 1.0 MHz, T_A = +85°C in the following equation which defines TC_C:

$$TC_C = \frac{C_T(+85^\circ C) - C_T(-65^\circ C)}{85 + 65} \cdot \frac{10^6}{C_R(25^\circ C)}$$

Accuracy limited by measurement of C_T to ± 0.1 pF.

TYPICAL DEVICE PERFORMANCE

FIGURE 1 – DIODE CAPACITANCE versus REVERSE VOLTAGE

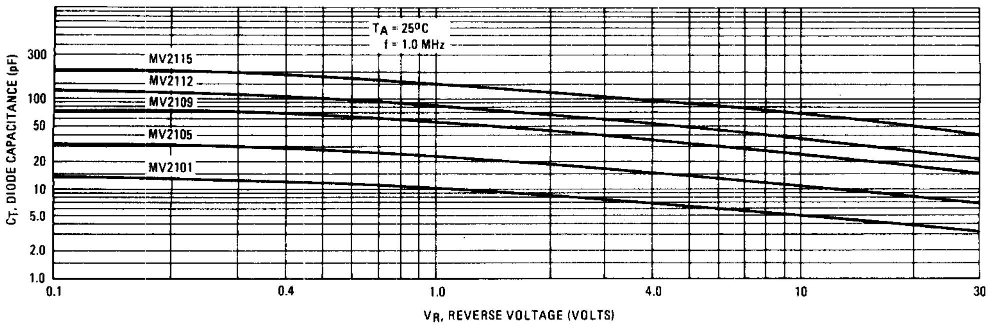


FIGURE 2 – NORMALIZED DIODE CAPACITANCE versus JUNCTION TEMPERATURE

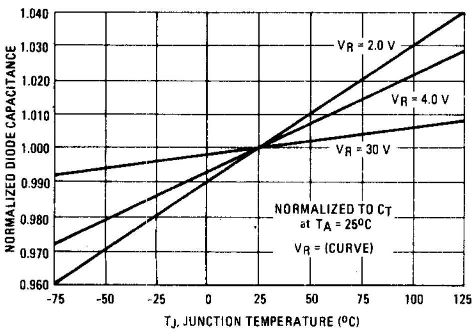


FIGURE 3 – REVERSE CURRENT versus REVERSE BIAS VOLTAGE

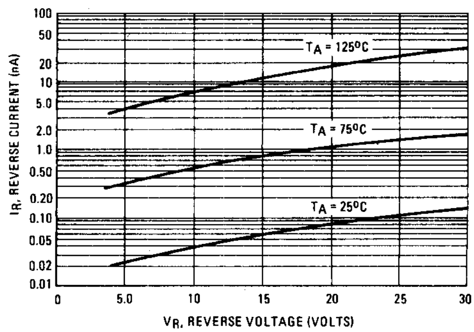


FIGURE 4 – FIGURE OF MERIT versus REVERSE VOLTAGE

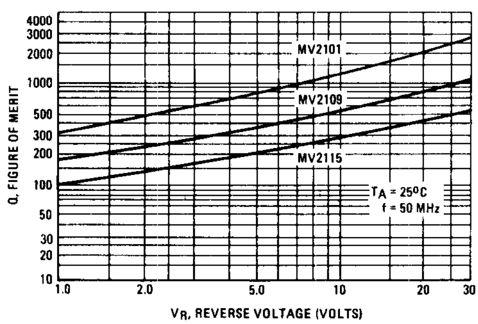
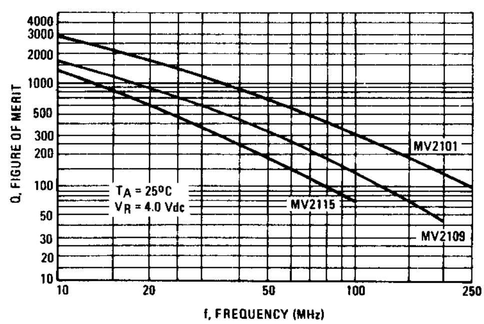


FIGURE 5 – FIGURE OF MERIT versus FREQUENCY



EPICAP VOLTAGE-VARIABLE CAPACITANCE DIODE DEVICE CONSIDERATIONS

A. Epicap Network Presentation

The equivalent circuit in Figure 6 shows the voltage capacitance and parasitic elements of an EPICAP diode. For design purposes at all but very high and very low frequencies, L_S, R_J, and C_C can be neglected. The simplified equivalent circuit of Figure 7 represents the diode under these conditions.

Definitions:

- C_J – Voltage-Variable Junction Capacitance
- R_S – Series Resistance (semiconductor bulk, contact, and lead resistance)
- C_C – Case Capacitance
- L_S – Series Inductance
- R_J – Voltage-Variable Junction Resistance (negligible above 100 kHz)

FIGURE 6

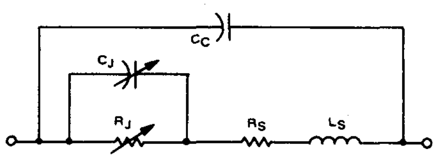
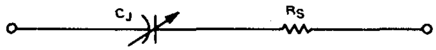


FIGURE 7



B. Epicap Capacitance versus Reverse Bias Voltage

The most important design characteristic of an EPICAP diode is the C_T versus V_R variation as shown in equations 1 and 2. Tuning Ratio, TR, between any two voltage points on curve of equation (2) is determined from equations (3) and (4).

$$C_T = C_C + C_J \quad (1)$$

$$C_T = C_C + \frac{C_o}{\left(1 + \frac{V_R}{\phi}\right)^{\gamma}} \quad (2)$$

$$\text{TR Junction} = \frac{C_{J1}}{C_{J2}} = \left(\frac{V_{R2} + \phi}{V_{R1} + \phi}\right)^{\gamma} \quad (3)$$

$$\text{TR Diode} = \frac{C_{T1}}{C_{T2}} = \frac{C_{J1} + C_C}{C_{J2} + C_C} \quad (4)$$

Conditions:

$C_o = C_J$ at $V_R = 0$
V_R = Reverse Bias (Volts)
γ, Diode Power Law, ≈ 0.44
ϕ, Contact Potential, ≈ 0.6 Volt
$C_c \approx 0.18$ pF

C. Epicap Capacitance versus Frequency

Variations in EPICAP effective capacitance, as a function of operating frequency, can be derived from a simplified equivalent circuit similar to that of Figure 6, but neglecting R_S and R_J. The admittance expression for such a circuit is given in equation 5. Examination of equation 5 yields the following information:

At low frequencies, $C_{eq} \approx C_J$; at very high frequencies ($f \approx \infty$) $C_{eq} \approx C_C$.

As frequency is increased from 1.0 MHz, C_{eq} increases until it is maximum at $\omega^2 = 1/L_S C_J$; and as ω^2 is increased from $1/L_S C_J$ toward infinity, C_{eq} increases from a very negative capacitance (inductance) toward $C_{eq} = C_C$, a positive capacitance.

Very simple calculations for C_{eq} at higher frequencies indicate the problems encountered when capacity measurements are made above 1.0 MHz. As ω approaches $\omega_o = 1/\sqrt{L_S C_J}$, small variations in L_S cause extreme variations in measured diode capacitance.

$$Y = j\omega C_{eq} = j\omega C_C + \frac{j\omega C_J}{1 - \omega^2 L_S C_J} \quad (5)$$

D. EPICAP Figure of Merit (Q) and Cutoff Frequency (f_{co})

The efficiency of EPICAP response to an input frequency is related to the Figure of Merit of the device as defined in equation 6. For very low frequencies, equation 7 applies whereas at high frequencies, where R_J can be neglected, equation 6 may be rewritten into the familiar form of equation 8.

Another useful parameter for EPICAP devices is the cutoff frequency (f_{co}), and is the frequency point where Q is equal to 1. Equation 9 gives this relationship.

$$Q = \frac{X_{Seq}}{R_{Seq}} \quad (6)$$

$$Q_{Lf} = \frac{\omega C_J R_J^2}{R_J + R_S(1 + \omega^2 C_J^2 R_J^2} \quad (7)$$

$$Q_{hf} = \frac{1}{\omega R_S C_{eq}} \quad (8)$$

$$f_{co} = Qf_{meas} \approx \frac{1}{2\pi R_S C_{BVR}} \quad (9)$$

E. Harmonic Generation Using EPICAPS

Efficient harmonic generation is possible with EPICAPS because of their high cutoff frequency and breakdown voltage. Since EPICAP junction capacitance varies inversely with the square root of the breakdown voltage, harmonic generator performance can be accurately predicted from various idealized models. Equation 10 gives the level of maximum input power for the EPICAP and equation 11 gives the relationships governing EPICAP circuit efficiency. In these equations, adequate heat sinking has been assumed.

$$P_{in(max)} = \frac{M(BV_R + \phi)^2}{R_S} \frac{f_{in}}{f_{co}} \quad (10)$$

$M(x2) = 0.0285$; $M(x3) = 0.0241$; $M(x4) = 0.196$

$$\text{Eff} = 1 - N \frac{f_{out}}{f_{co}} \quad (11)$$

$N(x2) = 20.8$; $N(x3) = 34.8$; $N(x4) = 62.5$

M and N are Constants